Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT223 surface-mountable plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

2. Features and benefits

- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate

3. Applications

- General purpose low power motor control
- · General purpose switching and phase control

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	-	12.5	A
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 110 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	-	1	А
Static characte	eristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	0.4	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	1.3	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	1.4	3	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$	-	3.8	7	mA
		T _j = 25 °C; <u>Fig. 7</u>				

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2—T1
2	T2	main terminal 2		G sym051
3	G	gate		·
4	T2	mainterminal 2	☐1 ☐2 ☐3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BT131W-600	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 110 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	1	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	12.5	А
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 \text{ms}$	-	13.8	Α
l ² t	I2t for fusing	t _p = 10 ms; SIN	-	0.78	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 1.5 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2+ G+	-	50	A/µs
		I_T = 1.5 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2+ G-	-	50	A/µs
		I _T = 1.5 A; I _G = 0.2 A; dI _G /dt = 0.2 A/μs; T2- G-	-	50	A/µs
		I_T = 1.5 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	Α
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

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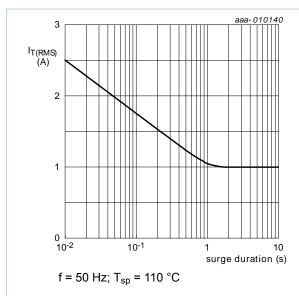


Fig. 1. RMS on-state current as a function of surge duration; maximum values

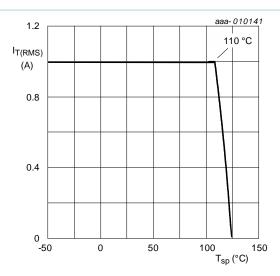


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

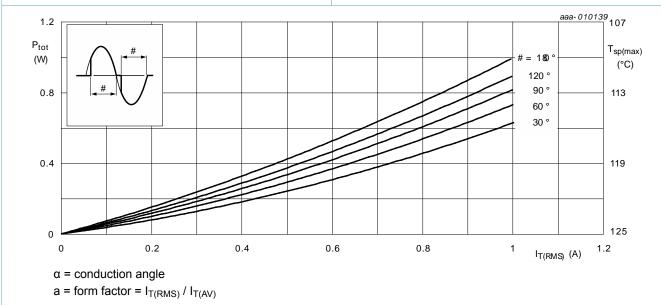


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

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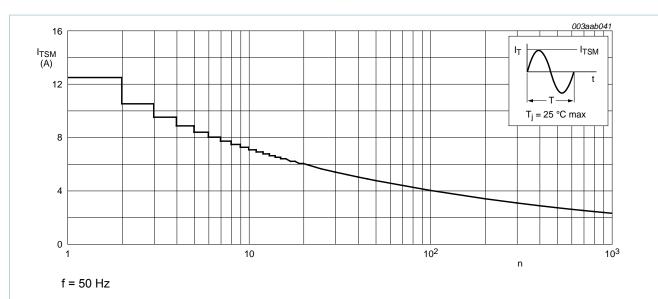
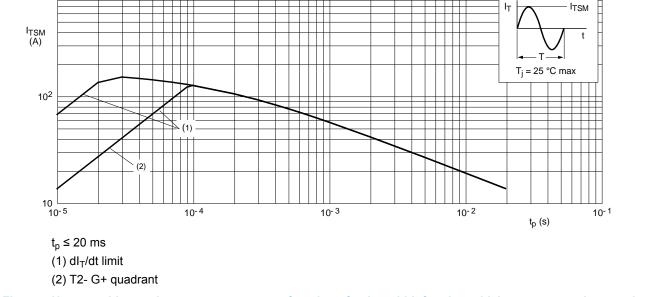


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



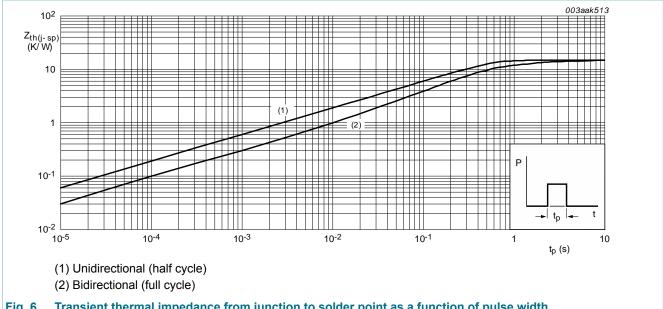
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Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	full cycle; Fig. 6	-	-	15	K/W
R _{th(j-a)}	thermal resistance	full cycle; for minimum footprint	-	156	-	K/W
	from junction to ambient	full cycle; for pad area	-	70	-	K/W



Transient thermal impedance from junction to solder point as a function of pulse width Fig. 6.

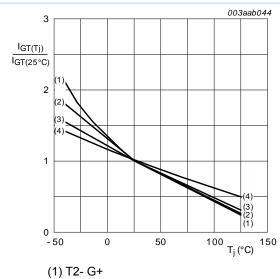
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9. Characteristics

Table 6 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	0.4	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	1.3	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	1.4	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	3.8	7	mA
l _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	1.2	5	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	4	8	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	1	5	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \text{ Fig. 8}$	-	2.5	8	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	1.3	5	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.2	0.3	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic o	characteristics		,			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; R_{GT1} = 1 kΩ; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; Fig. 12	10	20	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_D = 400 V; T_j = 125 °C; $dI_{com}/$ dt = 0.5 A/ms; I_T = 1 A; gate open circuit	2	-	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 1.5 A; V_D = 600 V; I_G = 0.1 A; dI_{G}/dt = 5 A/ μ s	-	2	-	μs

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- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

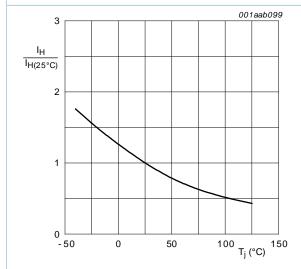


Fig. 9. Normalized holding current as a function of junction temperature

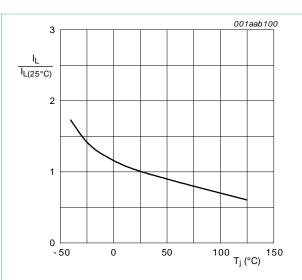
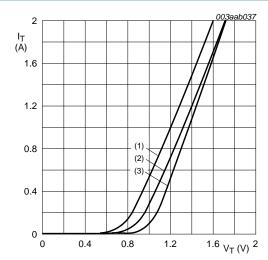


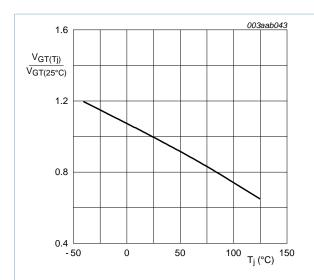
Fig. 8. Normalized latching current as a function of junction temperature

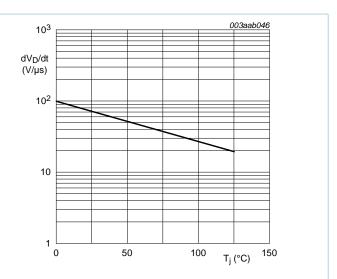


- $V_0 = 0.92 \text{ V}; R_s = 0.4 \Omega$
- (1) T_i = 125 °C; typical values
- (2) T_i = 125 °C; maximum values
- (3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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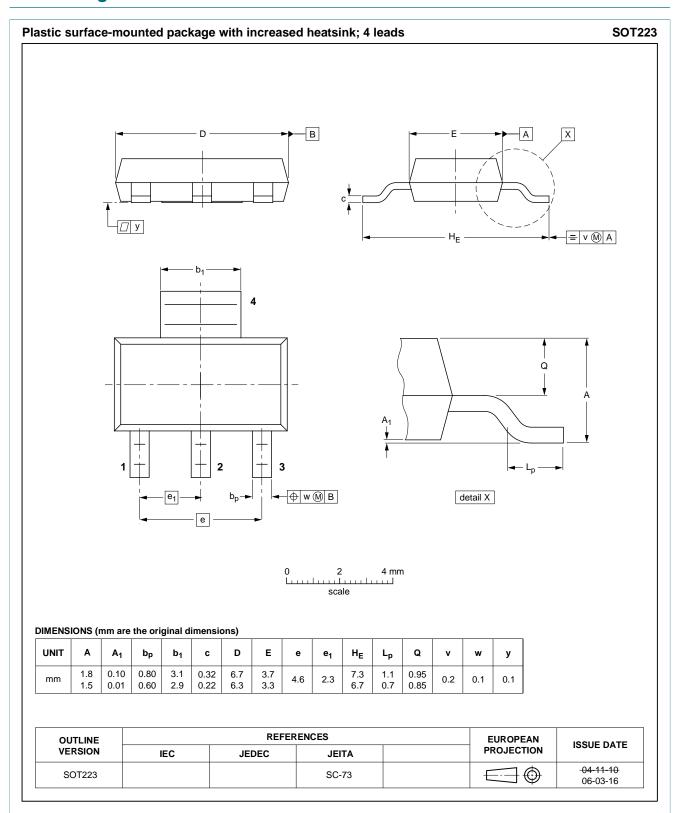


junction temperature

Fig. 11. Normalized gate trigger voltage as a function of junction temperature; typical values

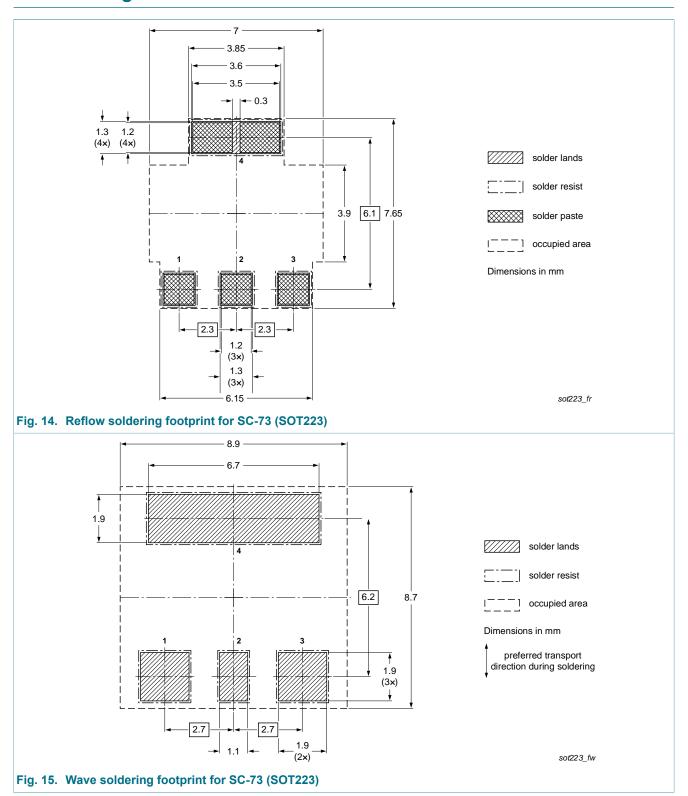
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10. Package outline



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11. Soldering



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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